

Silicon NPN Power Transistors

BU2506AF

DESCRIPTION

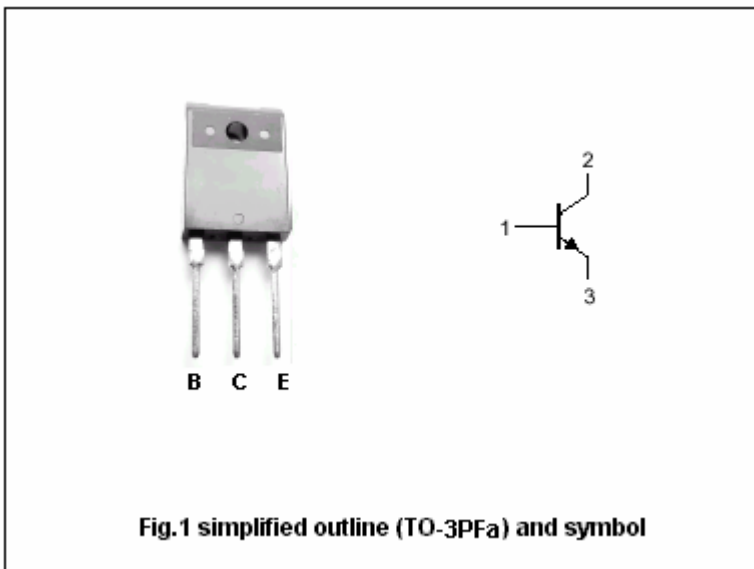
- With TO-3PFa package
- High voltage
- High speed switching

APPLICATIONS

- Intended for use in horizontal deflection circuits of colour TV receivers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CB0</sub>	Collector-base voltage	Open emitter	1500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	700	V
I <sub>C</sub>	Collector current (DC)		5	A
I <sub>CM</sub>	Collector current (Pulse)		8	A
I <sub>B</sub>	Base Collector current (DC)		3	A
I <sub>BM</sub>	Base current (Pulse)		5	A
P <sub>tot</sub>	Total power dissipation	T <sub>C</sub> =25°C	45	W
T <sub>j</sub>	Max.operating junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-65~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEQ(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA ; I <sub>B</sub> =0,	700			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA ; I <sub>C</sub> =0	7.5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =3A ; I <sub>B</sub> =0.79A			5.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =3A ; I <sub>B</sub> =0.79A			1.1	V
I <sub>CEs</sub>	Collector cut-off current	V <sub>CE</sub> =RatedV <sub>CE</sub> ; V <sub>BE</sub> =0 T <sub>j</sub> =125 °C			1.0 2.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7.5V ; I <sub>C</sub> =0			0.1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =0.3A ; V <sub>CE</sub> =5V		12		
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =3A ; V <sub>CE</sub> =5V	3.8	5.5	7.5	

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PACKAGE OUTLINE



Fig.2 Outline dimensions (unindicated tolerance:±0.30mm)